

* * * * * Welcome to STN International * * * * *

<u>NEWS 1</u>		Web Page URLs for STN Seminar Schedule - N. America
<u>NEWS 2</u>		"Ask CAS" for self-help around the clock
<u>NEWS 3</u>	FEB 28	PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS 4</u>	FEB 28	BABS - Current-awareness alerts (SDIs) available
<u>NEWS 5</u>	MAR 02	GBFULL: New full-text patent database on STN
<u>NEWS 6</u>	MAR 03	REGISTRY/ZREGISTRY - Sequence annotations enhanced
<u>NEWS 7</u>	MAR 03	MEDLINE file segment of TOXCENTER reloaded
<u>NEWS 8</u>	MAR 22	KOREAPAT now updated monthly; patent information enhanced
<u>NEWS 9</u>	MAR 22	Original IDE display format returns to REGISTRY/ZREGISTRY
<u>NEWS 10</u>	MAR 22	PATDPASPC - New patent database available
<u>NEWS 11</u>	MAR 22	REGISTRY/ZREGISTRY enhanced with experimental property tags
<u>NEWS 12</u>	APR 04	EPFULL enhanced with additional patent information and new fields
<u>NEWS 13</u>	APR 04	EMBASE - Database reloaded and enhanced
<u>NEWS 14</u>	APR 18	New CAS Information Use Policies available online
<u>NEWS 15</u>	APR 25	Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAPLUS and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications.
<u>NEWS 16</u>	APR 28	Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAPLUS
<u>NEWS 17</u>	MAY 23	GBFULL enhanced with patent drawing images
<u>NEWS 18</u>	MAY 23	REGISTRY has been enhanced with source information from CHEMCATS
<u>NEWS 19</u>	JUN 06	The Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available
<u>NEWS 20</u>	JUN 13	RUSSIAPAT: New full-text patent database on STN
<u>NEWS 21</u>	JUN 13	FRFULL enhanced with patent drawing images
<u>NEWS 22</u>	JUN 27	MARPAT displays enhanced with expanded G-group definitions and text labels
<u>NEWS 23</u>	JUL 01	MEDICONF removed from STN
<u>NEWS 24</u>	JUL 07	STN Patent Forums to be held in July 2005
<u>NEWS 25</u>	JUL 13	SCISEARCH reloaded
<u>NEWS 26</u>	JUL 20	Powerful new interactive analysis and visualization software, STN AnaVist, now available
<u>NEWS EXPRESS</u>	JUNE 13	CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005
<u>NEWS HOURS</u>		STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>		General Internet Information
<u>NEWS LOGIN</u>		Welcome Banner and News Items
<u>NEWS PHONE</u>		Direct Dial and Telecommunication Network Access to STN
<u>NEWS WWW</u>		CAS World Wide Web Site (general information)

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* * * * * STN Columbus * * * * *

FILE 'HOME' ENTERED AT 13:02:27 ON 28 JUL 2005

=> file inspec

COST IN U.S. DOLLARS	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'INSPEC' ENTERED AT 13:02:53 ON 28 JUL 2005

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FILE LAST UPDATED: 25 JUL 2005 <20050725/UP>
FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
THE BASIC INDEX >>>

=> s silicon carbide substrate

336202 SILICON
25696 CARBIDE
176648 SUBSTRATE
L1 46 SILICON CARBIDE SUBSTRATE
(SILICON (W) CARBIDE (W) SUBSTRATE)

=> s cmos

L2 58764 CMOS

=> s 1 and 2

1419292 1
1205084 2
L3 671700 1 AND 2

=> s l1 and l2

L4 0 L1 AND L2

=> s silicon carbide

336202 SILICON
25696 CARBIDE
L5 11054 SILICON CARBIDE
(SILICON (W) CARBIDE)

=> s l2 and l5

L6 27 L2 AND L5

=> d 16 1-27

L6 ANSWER 1 OF 27 INSPEC (C) 2005 IEE on STN

Full Text Reference

AN 2005:8487617 INSPEC DN A2005-16-0130C-023; B2005-08-0100-047;
C2005-08-0000-062
TI 27th International Spring Seminar on Electronics Technology (IEEE Cat.
No.04EX830).
SO Piscataway, NJ, USA: IEEE, 2005. 3 vol. 580 pp.
Conference: Bankya, Bulgaria, 13-16 May 2004
Price: CCCC 04/\$20.00
ISBN: 0-7803-8422-9
DT Conference Proceedings
CY United States
LA English

L6 ANSWER 2 OF 27 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:8096409 INSPEC DN B2004-10-2550G-039
 TI A 90 nm dual damascene hybrid (organic/inorganic) low-k-copper BEOL integration scheme.
 AU Dalton, T.J. (IBM Res. Div., Semicond. Res. & Dev. Center, Yorktown Heights, NY, USA); Cowley, A.; Clevenger, L.; La Tulipe, D.; Li, W.-K.; Kumar, K.; Simon, A.; Kaldor, S.; Yang, C.-C.; Lin, Y.-H.; Hoinkis, M.; Schacht, J.; Naujok, M.; Economikos, L.; Rovedo, N.; Olbrecht, A.; Wang, H.; Swift, A.; Li, B.; Chanda, K.; Lee, T.; Burrel, L.; Matusiewicz, G.; Fayaz, F.; Yang, S.; Yanagisawa, T.; Lu, N.; Angyal, M.; Dunn, D.; Ng, H.; Wann, C.; Crowder, S.; Chen, T.-C.
 SO Advanced Metallization Conference 2003 (AMC 2003)
 Editor(s): Ray, G.W.; Smy, T.; Ohla, T.; Tsujimura, M.
 Warrendale, PA, USA: Mater. Res. Soc., 2004. p.85-9 of xxiii+792 pp. 4 refs.
 Conference: Montreal, Que., Canada & Tokyo, Japan, 21-23 Oct 2003 & 29 Sept-1 Oct 2003
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L6 ANSWER 3 OF 27 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7936705 INSPEC DN B2004-05-2575F-182
 TI Polyimide sacrificial layer for an all-dry post-process surface micromachining module.
 AU Pham, H.T.M.; Bagolini, A.; de Boer, C.R.; Laros, J.M.W. (Inst. for Microelectron. & Submicron Technol., Delft Univ. of Technol., Netherlands); Pakula, L.; French, P.J.; Sarro, P.M.
 SO TRANSDUCERS '03. 12th International Conference on Solid-State Sensors, Actuators and Microsystems. Digest of Technical Papers (Cat. No.03TH8664) Piscataway, NJ, USA: IEEE, 2003. p.813-16 vol.1 of 2 vol.(xl+xxxix+1938) pp. 6 refs. Also available on CD-ROM in PDF format
 Conference: Boston, MA, USA, 8-12 June 2003
 Sponsor(s): IEEE; Electron Devices Soc
 Price: CCCC 0-7803-7731-1/03/\$17.00
 ISBN: 0-7803-7731-1
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L6 ANSWER 4 OF 27 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7884624 INSPEC DN B2004-04-2575F-008
 TI A CMOS compatible SiC accelerometer.
 AU Pakula, L.S.; Yang, H.; French, P.J. (DIMES, Delft Univ. of Technol., Netherlands)
 SO Proceedings of IEEE Sensors 2003 (IEEE Cat. No.03CH37498) Piscataway, NJ, USA: IEEE, 2003. p.761-4 Vol.2 of 1367 pp. 7 refs.
 Conference: Toronto, Ont., Canada, 22-24 Oct 2003
 Sponsor(s): IEEE Sensors Council
 Price: CCCC 0-7803-8133-5/03/\$17.00
 ISBN: 0-7803-8133-5

DT Conference Article
 TC Application
 CY United States
 LA English

L6 ANSWER 5 OF 27 INSPEC (C) 2005 IEE on STN



AN 2004:7862337 INSPEC DN B2004-03-2550G-124
 TI A novel graded antireflective coating with built-in hardmask properties enabling 65nm and below **CMOS** device patterning.
 AU Babich, K. (IBM T. J. Watson Res. Center, Yorktown Heights, NY, USA); Fukiage, N.; Mahorowala, A.; Halle, S.; Bunner, T.; Pfeiffer, D.; Mochiki, H.; Ashigaki, S.; Xia, A.; Angelopoulos, M.
 SO IEEE International Electron Devices Meeting 2003
 Piscataway, NJ, USA: IEEE, 2003. p.28.5.1-4 of 999 pp. 5 refs.
 Conference: Washington, DC, USA, 8-10 Dec 2003
 Price: CCCC 0-7803-7872-5/03/\$17.00
 ISBN: 0-7803-7872-5
 DT Conference Article
 TC New Development; Practical; Experimental
 CY United States
 LA English

L6 ANSWER 6 OF 27 INSPEC (C) 2005 IEE on STN



AN 2003:7509357 INSPEC DN B2003-02-2550F-065
 TI Advanced metal barrier free Cu damascene interconnects with PECVD **silicon carbide** barriers for 90/65-nm BEOL technology.
 AU Wu, Z.C.; Lu, Y.C.; Chiang, C.C.; Chen, M.C.; Chen, B.T.; Wang, G.J.; Chen, Y.T.; Huang, J.L.; Jang, S.M.; Liang, M.S. (Dept. of Dielectric & CMP, Taiwan Semicond. Manuf. Co., Hsinchu, Taiwan)
 SO International Electron Devices Meeting. Technical Digest (Cat. No.02CH37358)
 Piscataway, NJ, USA: IEEE, 2002. p.595-8 of 957 pp. 5 refs.
 Conference: San Francisco, CA, USA, 8-11 Dec 2002
 Sponsor(s): Electron. Devices Soc. IEEE
 Price: CCCC 0-7803-7462-2/02/\$17.00
 ISBN: 0-7803-7462-2
 DT Conference Article
 TC Application; Practical; Experimental
 CY United States
 LA English

L6 ANSWER 7 OF 27 INSPEC (C) 2005 IEE on STN



AN 2000:6610704 INSPEC DN B2000-07-2570D-006
 TI Study of the **silicon carbide** integrate circuits technique.
 AU Wang Jian-Ping; Hao Yue; Peng Jun (Res. Inst. of Microelectron., Xidian Univ., Xi'an, China)
 SO Journal of Xidian University (April 2000) vol.27, no.2, p.228-32. 8 refs.
 Published by: Xidian Univ
 CODEN: XDKXEP ISSN: 1001-2400
 SICI: 1001-2400(200004)27:2L.228:SSCI;1-7
 DT Journal
 TC Experimental
 CY China
 LA Chinese

L6 ANSWER 8 OF 27 INSPEC (C) 2005 IEE on STN



AN 2000:6475744 INSPEC DN B2000-02-2570D-057
 TI Submicron **silicon carbide CMOS** for smartpower applications.
 AU Kornegay, K.T. (Sch. of Electr. Eng., Cornell Univ., Ithaca, NY, USA)
 SO 11th International Symposium on Power Semiconductor Devices and ICs.
 ISPSD'99 Proceedings (Cat. No.99CH36312)
 Piscataway, NJ, USA: IEEE, 1999. p.297-300 of xxiii+359 pp. 6 refs.
 Conference: Toronto, Ont., Canada, 26-28 May 1999
 Sponsor(s): IEEE Electron Devices Soc.; Inst. Elec. Eng. of Japan
 Price: CCCC 0 7803 5290 4/99/\$10.00
 ISBN: 0-7803-5290-4
 DT Conference Article
 TC Application; Practical; Experimental
 CY United States
 LA English

L6 ANSWER 9 OF 27 INSPEC (C) 2005 IEE on STN



AN 1999:6198509 INSPEC DN B1999-05-2570D-001
 TI Recent progress of submicron **CMOS** using 6H-SiC for smart power applications.
 AU Man Pio Lam (Motorola Inc., Tempe, AZ, USA); Kornegay, K.T.
 SO IEEE Transactions on Electron Devices (March 1999) vol.46, no.3, p.546-54.
 16 refs.
 Doc. No.: S0018-9383(99)01683-4
 Published by: IEEE
 Price: CCCC 0018-9383/99/\$10.00
 CODEN: IETDAI ISSN: 0018-9383
 SICI: 0018-9383(199903)46:3L:546:RPSC;1-I
 DT Journal
 TC Application; Experimental
 CY United States
 LA English

L6 ANSWER 10 OF 27 INSPEC (C) 2005 IEE on STN



AN 1999:6164781 INSPEC DN B1999-03-2570P-008
 TI A **silicon carbide CMOS** intelligent gate driver circuit with stable operation over a wide temperature range.
 AU Jian-Song Chen (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA); Kornegay, K.T.; Sei-Hyung Ryu
 SO IEEE Journal of Solid-State Circuits (Feb. 1999) vol.34, no.2, p.192-204.
 14 refs.
 Doc. No.: S0018-9200(99)00987-7
 Published by: IEEE
 Price: CCCC 0018-9200/99/\$10.00
 CODEN: IJSCBC ISSN: 0018-9200
 SICI: 0018-9200(199902)34:2L:192:SCCI;1-F
 DT Journal
 TC Application; Practical; Theoretical; Experimental
 CY United States
 LA English

L6 ANSWER 11 OF 27 INSPEC (C) 2005 IEE on STN



AN 1999:6161866 INSPEC DN B1999-03-1210-012
 TI A **silicon carbide CMOS** intelligent gate driver circuit.
 AU Jian-Song Chen; Sei-Hyung Ryu; Kornegay, K.T. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
 SO Conference Record of 1998 IEEE Industry Applications Conference. Thirty-Third IAS Annual Meeting (Cat. No.98CH36242)
 New York, NY, USA: IEEE, 1998. p.963-6 vol.2 of 3 vol. xxx+2410 pp. 4 refs.
 Conference: St. Louis, MO, USA, 12-15 Oct 1998
 Price: CCCC 0 7803 4943 1/98/\$10.00
 ISBN: 0-7803-4943-1
 DT Conference Article
 TC Theoretical; Experimental
 CY United States
 LA English

L6 ANSWER 12 OF 27 INSPEC (C) 2005 IEE on STN



AN 1998:6116504 INSPEC DN B9902-1220-006
 TI Design of a process variation tolerant **CMOS** opamp in 6H-SiC technology for high-temperature operation.
 AU Jian-Song Chen (Texas Instrum. Inc., Dallas, TX, USA); Kornegay, K.T.
 SO IEEE Transactions on Circuits and Systems I: Fundamental Theory and Applications (Nov. 1998) vol.45, no.11, p.1159-71. 17 refs.
 Doc. No.: S1057-7122(98)07720-4
 Published by: IEEE
 Price: CCCC 1057-7122/98/\$10.00
 CODEN: ITCAEX ISSN: 1057-7122
 SICI: 1057-7122(199811)45:11L:1159:DPVT;1-1
 DT Journal
 TC Application; Practical; Experimental
 CY United States
 LA English

L6 ANSWER 13 OF 27 INSPEC (C) 2005 IEE on STN



AN 1998:6111440 INSPEC DN B9901-1280-007
 TI High-temperature mixed-signal ICs using **silicon carbide CMOS** technology.
 AU Jian-Song Chen; Sei-Hung Ryu (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA); Kornegay, K.T.
 SO 1998 Fourth International High Temperature Electronics Conference. HITEC (Cat. No.98EX145)
 New York, NY, USA: IEEE, 1998. p.292-5 of vii+332 pp. 4 refs.
 Conference: Albuquerque, NM, USA, 14-18 June 1998
 Sponsor(s): Air Force Res. Lab.; Sandia Nat. Lab.; Team Speciality Products; Cree Res.; Honeywell Solid State Electron. Center; AlliedSignal; Northrop Grumman Corp.; Electron. Devices Soc.; Components Packaging & Manuf. Technol. Soc
 Price: CCCC 0 7803 4540 1/98/\$10.00
 ISBN: 0-7803-4540-1
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L6 ANSWER 14 OF 27 INSPEC (C) 2005 IEE on STN



AN 1998:6045429 INSPEC DN B9811-2575-031
 TI PECVD **silicon carbide** as a chemically resistant material for micromachined transducers.
 AU Flannery, A.F.; Mourlas, N.J.; Storment, C.W. (Stanford Univ., CA, USA); Tsai, S.; Tan, S.H.; Heck, J.; Monk, D.; Kim, T.; Gogoi, B.; Kovacs, G.T.A.
 SO Sensors and Actuators A (Physical) (1 Oct. 1998) vol.A70, no.1-2, p.48-55. 12 refs.
 Doc. No.: S0924-4247(98)00111-3
 Published by: Elsevier
 Price: CCCC 0924-4247/98/\$19.00
 CODEN: SAAPEB ISSN: 0924-4247
 SICI: 0924-4247(19981001)A70:1/2L:48:PSCC;1-1
 Conference: 9th International Solid State Sensors and Actuators Conference (Transducers '97). Chicago, IL, USA, 16-19 June 1997
 Sponsor(s): IEEE Electron Devices Soc
 DT Conference Article; Journal
 TC Experimental
 CY Switzerland
 LA English

L6 ANSWER 15 OF 27 INSPEC (C) 2005 IEE on STN



AN 1998:5992549 INSPEC DN B9809-1220-012
 TI A constant input transconductance and rail-to-rail input/output swing SiC **CMOS** op amp.
 AU Jian-Song Chen; Kornegay, K.T. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
 SO ISCAS '98. Proceedings of the 1998 IEEE International Symposium on Circuits and Systems (Cat. No.98CH36187)
 New York, NY, USA: IEEE, 1998. p.241-4 vol.1 of 6 vol. (xlv+603+489+674+615+557+656) pp. 6 refs.
 Conference: Monterey, CA, USA, 31 May-3 June 1998
 Price: CCCC 0 7803 4455 3/98/\$10.00
 ISBN: 0-7803-4455-3
 DT Conference Article
 TC New Development; Practical; Theoretical
 CY United States
 LA English

L6 ANSWER 16 OF 27 INSPEC (C) 2005 IEE on STN



AN 1998:5900992 INSPEC DN B9806-1280-005
 TI Design of a **silicon carbide** smart power switch with stable operation over a wide temperature range.
 AU Jian-Song Chen; Kornegay, K.T. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
 SO Proceedings of Midwest Symposium on Circuits and Systems Dedicated to the Memory of Professor Mac Van Valkenburg (Cat. No.97CH36010)
 Editor(s): Soderstrand, M.A.; Michael, S.
 New York, NY, USA: IEEE, 1998. p.123-6 vol.1 of 2 vol. lvi+1480 pp. 12 refs.
 Conference: Sacramento, CA, USA, 3-6 Aug 1997
 Sponsor(s): Univ. California Davis; IEEE Circuits & Syst. Soc
 Price: CCCC 0 7803 3694 1/97/\$10.00
 ISBN: 0-7803-3694-1

DT Conference Article
 TC Application; Practical
 CY United States
 LA English

L6 ANSWER 17 OF 27 INSPEC (C) 2005 IEE on STN

Full Text

AN 1998:5878529 INSPEC DN B9805-7230G-026
 TI An uncooled IR imager with 5 mK NEDT.
 AU Amantea, R.; Knoedler, C.M.; Pantuso, F.P.; Patel, V.K.; Sauer, D.J.; Tower, J.R.
 SO Proceedings of the SPIE - The International Society for Optical Engineering (1997) vol.3061, p.210-22. 3 refs.
 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/97/\$10.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(1997)3061L:210:UIWN;1-X
 Conference: Infrared Technology and Applications XXIII. Orlando, FL, USA, 20-25 April 1997
 Sponsor(s): SPIE
 DT Conference Article; Journal
 TC Practical; Experimental
 CY United States
 LA English

L6 ANSWER 18 OF 27 INSPEC (C) 2005 IEE on STN

Full Text

AN 1997:5751673 INSPEC DN B9712-2575-059
 TI PECVD **silicon carbide** for micromachined transducers.
 AU Flannery, A.F.; Mourlas, N.J.; Storment, C.W. (Stanford Univ., CA, USA); Tsai, S.; Tan, S.H.; Kovacs, G.T.A.
 SO Transducers 97. 1997 International Conference on Solid-State Sensors and Actuators. Digest of Technical Papers (Cat. No.97TH8267)
 New York, NY, USA: IEEE, 1997. p.217-20 vol.1 of 2 vol. 1525 pp. 8 refs.
 Conference: Chicago, IL, USA, 16-19 June 1997
 Sponsor(s): IEEE Electron Devices Soc
 Price: CCCC 0 7803 3829 4/97/\$10.00
 ISBN: 0-7803-3829-4
 DT Conference Article
 TC Application; Experimental
 CY United States
 LA English

L6 ANSWER 19 OF 27 INSPEC (C) 2005 FIZ KARLSRUHE on STN

Full Text

AN 1997:5750761 INSPEC DN B9712-2570F-007
 TI **Silicon carbide** MOSFET integrated circuit technology.
 AU Brown, D.M.; Downey, E.; Ghezze, M.; Kretchmer, J.; Krishnamurthy, V.; Hennessy, W.; Michon, G. (Gen. Electr. Corp. Res. & Dev. Center, Schenectady, NY, USA)
 SO Physica Status Solidi A (16 July 1997) vol.162, no.1, p.459-79. 51 refs.
 Published by: Akademie Verlag
 Price: CCCC 0031-8965/97/\$10.00+0.25
 CODEN: PSSABA ISSN: 0031-8965
 SICI: 0031-8965(19970716)162:1L:459:SCMI;1-O
 DT Journal
 TC General Review; Practical

CY Germany, Federal Republic of
LA English

L6 ANSWER 20 OF 27 INSPEC (C) 2005 IEE on STN

Full
Text

AN 1997:5730807 INSPEC DN B9712-1265-001
TI 6H-SiC CMOS digital ICs operating on a 5 V power supply.
AU Ryu, S.; Kornegay, K.T.; Cooper, J.A., Jr.; Melloch, M.R. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
SO 1997 55th Annual Device Research Conference Digest (Cat. No.97TH8279)
New York, NY, USA: IEEE, 1997. p.38-9 of 175 pp. 3 refs.
Conference: Fort Collins, CO, USA, 23-25 June 1997
Sponsor(s): IEEE Electron Devices Soc
ISBN: 0-7803-3911-8
DT Conference Article
TC Practical; Experimental
CY United States
LA English

L6 ANSWER 21 OF 27 INSPEC (C) 2005 IEE on STN

Full
Text

AN 1997:5716833 INSPEC DN B9711-1220-015
TI Design of a silicon carbide CMOS power OPAMP for stable operation at elevated temperatures.
AU Jian-Song Chen; Kornegay, K.T. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
SO Proceedings of 1997 IEEE International Symposium on Circuits and Systems. Circuits and Systems in the Information Age. ISCAS '97 (Cat. No.97CH35987)
New York, NY, USA: IEEE, 1997. p.157-60 vol.1 of 4 vol. lxvi+2832 pp. 12 refs.
Conference: Hong Kong, 9-12 June 1997
Price: CCCC 0 7803 3583 X/97/\$10.00
ISBN: 0-7803-3583-X
DT Conference Article
TC Theoretical
CY United States
LA English

L6 ANSWER 22 OF 27 INSPEC (C) 2005 IEE on STN

Full
Text

AN 1997:5703878 INSPEC DN B9711-2560R-014
TI Silicon carbide for power devices.
AU Palmour, J.W.; Singh, R.; Glass, R.C.; Kordina, O.; Carter, C.H., Jr. (Cree Res. Inc., Durham, NC, USA)
SO ISPSD '97. 1997 IEEE International Symposium on Power Semiconductor Devices and ICs (Cat. No.97CH36086)
New York, NY, USA: IEEE, 1997. p.25-32 of 375 pp. 31 refs.
Conference: Weimar, Germany, 26-29 May 1997
Sponsor(s): VDE; IEEE Electron Devices Soc.; IEE Japan; EUREL
Price: CCCC 0 7803 3993 2/97/\$10.00
ISBN: 0-7803-3993-2
DT Conference Article
TC Application; General Review; Practical
CY United States
LA English

L6 ANSWER 23 OF 27 INSPEC (C) 2005 IEE on STN



AN 1997:5573501 INSPEC DN B9706-1220-014
 TI Class-AB SiC CMOS power opamp with stable voltage gain over wide temperature range.
 AU Chen, J.-S.; Kornegay, K.T. (Sch. of Electr. & Comput. Eng., Purdue Univ., West Lafayette, IN, USA)
 SO IEE Proceedings-Circuits, Devices and Systems (Feb. 1997) vol.144, no.1, p.22-8. 13 refs.
 Published by: IEE
 Price: CCCC 1350-2409/97/\$10.00
 CODEN: ICDSE7 ISSN: 1350-2409
 SICI: 1350-2409(199702)144:1L:22:CCPO;1-F
 DT Journal
 TC Application; Practical; Theoretical; Experimental
 CY United Kingdom
 LA English

L6 ANSWER 24 OF 27 INSPEC (C) 2005 IEE on STN



AN 1996:5267064 INSPEC DN B9606-2560J-043
 TI Feasibility of 4.5 kV and 10 kV **silicon carbide** IGBTs.
 AU Bakowski, M.; Gustafsson, U.; Ramberg, L.P. (Ind. Microelectron. Center, Kista, Sweden)
 SO ESSDERC '94. Proceedings of the 24th European Solid State Device Research Conference
 Editor(s): Hill, C.; Ashburn, P.
 Gif sur Yvette, France: Editions Frontieres, 1994. p.761-4 of xxxiii+854 pp. 5 refs.
 Conference: Edinburgh, UK, 11-15 Sept 1994
 Sponsor(s): IEEE
 ISBN: 2-86332-157-9
 DT Conference Article
 TC Practical; Experimental
 CY France
 LA English

L6 ANSWER 25 OF 27 INSPEC (C) 2005 IEE on STN



AN 1993:4417945 INSPEC DN B9307-0170J-016
 TI Low temperature ceramic coatings for chip-on-board assemblies.
 AU Camilletti, R.; Chandra, G. (Dow Corning Corp., Midland, MI, USA)
 SO Surface Mount International Conference and Exposition. Proceedings of the Technical Program
 Edina, MN, USA: Surface Mount Int, 1992. p.71-83 vol.1 of 2 vol. 1251 pp. 9 refs. Availability: Surface Mount Int., 13760 Noel Road, Suite 500, Dallas, TX 75240, USA
 Conference: San Jose, CA, USA, 30 Aug-3 Sept 1992
 DT Conference Article
 TC Application; Practical; Experimental
 CY United States
 LA English

L6 ANSWER 26 OF 27 INSPEC (C) 2005 IEE on STN



AN 1991:4000733 INSPEC DN B91069837
 TI Low temperature ceramic coatings for environmental protection of